Moon-Kyu Cho

List of Publications by Year
in descending order

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32	303	840776 11	888059 17
papers	citations	h-index	g-index

32	32	32	283
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Design Methodology for a Wideband, Low Insertion Loss, Digital Step Attenuator in SiGe BiCMOS Technology. IEEE Transactions on Circuits and Systems II: Express Briefs, 2022, 69, 744-748.	3.0	5
2	Investigation of f _T-Doubler Technique to Improve RF Performance of Inverse-Mode SiGe HBTs. IEEE Microwave and Wireless Components Letters, 2020, 30, 873-875.	3.2	5
3	A New Wideband, Low Insertion Loss, High Linearity SiGe RF Switch. IEEE Microwave and Wireless Components Letters, 2020, 30, 985-988.	3.2	23
4	A Two-Way Wideband Active SiGe BiCMOS Power Divider/Combiner for Reconfigurable Phased Arrays With Controllable Beam Width. IEEE Access, 2020, 8, 2578-2589.	4.2	2
5	Design of an 18â€“50 GHz SiGe HBT Cascode Non-uniform Distributed Power Amplifier. , 2020, , .		1
6	A New Wideband, Low Insertion Loss SiGe Digital Step Attenuator A New Wideband, Low Insertion Loss SiGe Digital Step Attenuator. , 2020, , .		2
7	A 2-20 GHz SiGe Amplitude Control Circuit with Differential Signal Selectivity for Wideband Reconfigurable Electronics. , 2019, , .		1
8	Best Practices for Using Electrostatic Discharge Protection Techniques for Single-Event Transient Mitigation. IEEE Transactions on Nuclear Science, 2019, 66, 240-247.	2.0	3
9	p-n-p-Based RF Switches for the Mitigation of Single-Event Transients in a Complementary SiGe BiCMOS Platform. IEEE Transactions on Nuclear Science, 2018, 65, 391-398.	2.0	6
10	An Electrostatic Discharge Protection Circuit Technique for the Mitigation of Single-Event Transients in SiGe BiCMOS Technology. IEEE Transactions on Nuclear Science, 2018, 65, 426-431.	2.0	4
11	Design and Analysis of a Low Loss, Wideband Digital Step Attenuator With Minimized Amplitude and Phase Variations. IEEE Journal of Solid-State Circuits, 2018, 53, 2202-2213.	5.4	57
12	Cryogenic Characterization of RF Low-Noise Amplifiers Utilizing Inverse-Mode SiGe HBTs for Extreme Environment Applications. IEEE Transactions on Device and Materials Reliability, 2018, 18, 613-619.	2.0	0
13	A SiGe-BiCMOS Wideband Active Bidirectional Digital Step Attenuator With Bandwidth Tuning and Equalization. IEEE Transactions on Microwave Theory and Techniques, 2018, 66, 3866-3876.	4.6	13
14	SiGe HBT Profiles With Enhanced Inverse-Mode Operation and Their Impact on Single-Event Transients. IEEE Transactions on Nuclear Science, 2018, 65, 399-406.	2.0	9
15	A 28-GHz Switchless, SiGe Bidirectional Amplifier Using Neutralized Common-Emitter Differential Pair. IEEE Microwave and Wireless Components Letters, 2018, 28, 717-719.	3.2	6
16	A multimode phase shifter for S-band phased array antenna. Microwave and Optical Technology Letters, 2018, 60, 1921-1924.	1.4	4
17	On the Application of Inverse-Mode SiGe HBTs in RF Receivers for the Mitigation of Single-Event Transients. IEEE Transactions on Nuclear Science, 2017, 64, 1142-1150.	2.0	9
18	Encapsulated Organic Package Technology for Wideband Integration of Heterogeneous MMICs. IEEE Transactions on Microwave Theory and Techniques, 2017, 65, 438-448.	4.6	11

#	Article	IF	Citations
19	The Use of Inverse-Mode SiGe HBTs as Active Gain Stages in Low-Noise Amplifiers for the Mitigation of Single-Event Transients. IEEE Transactions on Nuclear Science, 2017, 64, 359-366.	2.0	8
20	A SiGe-BiCMOS Wideband (2â€“22 GHz) Active Power Divider/Combiner Circuit Supporting Bidirectional Operation. IEEE Transactions on Microwave Theory and Techniques, 2016, 64, 4676-4684.	4.6	12
21	An Investigation of the Use of Inverse-Mode SiGe HBTs as Switching Pairs for SET-Mitigated RF Mixers. IEEE Transactions on Nuclear Science, 2016, 63, 1099-1108.	2.0	13
22	A Compact, Wideband Lumped-Element Wilkinson Power Divider/Combiner Using Symmetric Inductors with Embedded Capacitors. IEEE Microwave and Wireless Components Letters, 2016, 26, 595-597.	3.2	19
23	Inverse classâ€‹<scp>F</scp><scp>X</scp>â€‹band <scp>S</scp>i<scp>G</scp>e <scp>HBT</scp> power amplifier with 44% <scp>PAE</scp> and 24.5 d<scp>B</scp>m peak output power. Microwave and Optical Technology Letters, 2016, 58, 2868-2871.	1.4	1
24	Co-design of a SiGe BiCMOS X-band, asymmetric, low insertion loss, high power handling SPDT Switch and an Ultra Low Noise LNA for next-generation T/R modules. , 2016, , .		3
25	Wideband active bi-directional SiGe digital step attenuator using an active DPDT switch. , 2016, , .		1
26	A Compact, Active SiGe Power Divider With Multi-Octave Bandwidth. IEEE Microwave and Wireless Components Letters, 2016, 26, 945-947.	3.2	6
27	An Active Bi-Directional SiGe DPDT Switch With Multi-Octave Bandwidth. IEEE Microwave and Wireless Components Letters, 2016, 26, 279-281.	3.2	13
28	Advantages of utilizing throughâ€‹siliconâ€‹vias in <scp>SiGe</scp> HBT RF lowâ€‹noise amplifier design. Microwave and Optical Technology Letters, 2015, 57, 2703-2706.	1.4	1
29	Optimization of SiGe HBT RF Switches for Single-Event Transient Mitigation. IEEE Transactions on Nuclear Science, 2015, 62, 3057-3063.	2.0	8
30	A Switchless CMOS Bi-Directional Distributed Gain Amplifier With Multi-Octave Bandwidth. IEEE Microwave and Wireless Components Letters, 2013, 23, 611-613.	3.2	23
31	Compact Xâ€‹band CMOS bidirectional gain amplifier without T/R switches. Electronics Letters, 2013, 49, 66-68.	1.0	11
32	An X-Band 5 Bit Phase Shifter With Low Insertion Loss in 0.18 $mu{m m}$ SOI Technology. IEEE Microwave and Wireless Components Letters, 2012, 22, 648-650.	3.2	23